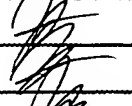
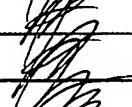
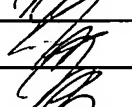
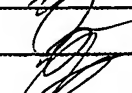
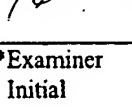
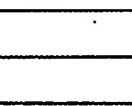
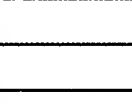
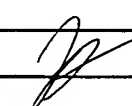
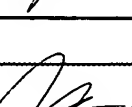


U.S. Department of Commerce, Patent and Trademark	Atty. Docket No.	Application No.
INFORMATION DISCLOSURE STATEMENT BY APPLICANT (Use several sheets if necessary) (Form PTO-1449)	SN DK.272US0	10/002,696
	Applicants	Conf. No.
	Eliyahou Harari et al.	4652
	Filing Date	Art Group
	October 31, 2001	2814

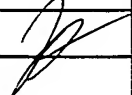
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	1	6,670,240 B2	12/30/03	Ogura et al.			
	2	6,413,821 B1	7/2/02	Ebina et al.			
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Foreign Patent Documents

							Translation	
		Document	Date	Country	Class	Subclass	Yes	No
	10	11224940	8/17/99	Japan			Abstract	X

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	11	S. Ogura et al., "Low Voltage, Low Current, High Speed Program Step Split Gate Cell With Ballistic Direct Injection for EEPROM/Flash", 1998, IEDM Technical Digest, 36.5, pp. 987-990.
	12	F.I. Hampton et al., "Space Charge Distribution Limitation on Scale Down of MNOS Memory Devices", 1979, IEDM Technical Digest, pp. 374-377.
	13	Eiichi Suzuki et al., "A Low-Voltage Alterable EEPROM With Metal-Oxide-Nitride-Oxide-Semiconductor (MONOS) Structures", IEEE Transactions on Electron Devices, Vol. ED-30, No. 2, February, 1983, pp. 122-128.

Examiner  Date Considered 2/17/05

*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with your communication to applicant.

U.S. Department of Commerce, Patent and Trademark				Atty. Docket No.		Application No.	
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				Eliyahou Harari et al.		4652	
				Filing Date		Art Group	
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		Document	Date	Country	Class	Subclass	Yes	No

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21	Y. Tarui et al., "Electrically Reprogrammable Nonvolatile Semiconductor Memory", IEEE Journal of Solid State Circuits, Vol, SC-7, No. 5, October 1972, pp. 369-375.
22	Boaz Eitan et al., "Can NROM, a 2 Bit, Trapping Storage NMV Cell, Give a Real Challenge to Floating Gate Cells?", Extended Abstracts, 1999 Conference on Solid State Devices and Materials, Tokyo, 1999, pp. 522-524.

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